

DCR4660H65



Phase Control Thyristor

Preliminary Information

DS6119- 2August 2013 (LN30818)

FEATURES

- Double Side Cooling
- High Surge Capability

APPLICATIONS

- High Power Drives
- High Voltage Power Supplies
- Static Switches

VOLTAGE RATINGS

Part and Repetitive Peak Ordering Voltages Number V _{DRM} and V _{RRM} V		Conditions	
DCR4660H65* DCR4660H60 DCR4660H55	6500 6000 5500	$\begin{array}{l} T_{vj} = -40^{\circ}C \ to \ 125^{\circ}C, \\ I_{DRM} = I_{RRM} = 600 mA, \\ V_{DRM}, \ V_{RRM} \ t_p = 10 ms, \\ V_{DSM} \& \ V_{RSM} = \\ V_{DRM} \& \ V_{RRM} \ + 100 V \\ respectively \end{array}$	

Lower voltage grades available. *6200V @ -40° C, 6500V @ 0° C

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

DCR4660H65

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

KEY PARAMETERS

V _{DRM}	6500V
I _{T(AV)}	4660A
I _{TSM}	69250A
dV/dt*	2000V/µs
dl/dt	200A/µs
I _{TSM} dV/dt*	2000V/µs

* Higher dV/dt selections available

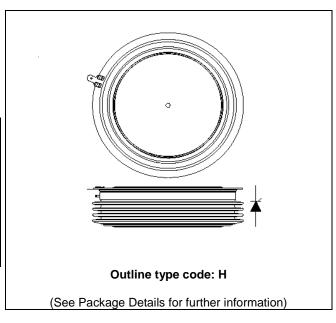


Fig. 1 Package outline





CURRENT RATINGS

 $T_{case} = 60^{\circ}C$ unless stated otherwise

Symbol	Parameter	Test Conditions		Units
Double Side Cooled				
I _{T(AV)}	Mean on-state current	Half wave resistive load	4660	А
I _{T(RMS)}	RMS value	-	7320	А
Ι _Τ	Continuous (direct) on-state current	-	6850	А

SURGE RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
I _{TSM}	Surge (non-repetitive) on-state current	10ms half sine, $T_{case} = 125^{\circ}C$	69.25	kA
l ² t	I ² t for fusing	$V_R = 0$	24.0	MA ² s

THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditions		Min.	Max.	Units
R _{th(j-c)}	Thermal resistance – junction to case	Double side cooled	DC	-	0.004255	°C/W
		Single side cooled	Anode DC	-	0.008	°C/W
			Cathode DC	-	0.0093	°C/W
R _{th(c-h)}	Thermal resistance – case to heatsink	Clamping force 135.0kN	Double side	-	0.0009	°C/W
		(with mounting compound)	Single side	-	0.0018	°C/W
T_{vj}	Virtual junction temperature	Blocking V _{DRM} / V _{RRM}		-	125	°C
T _{stg}	Storage temperature range			-55	125	°C
Fm	Clamping force			120	155	kN





DYNAMIC CHARACTERISTICS

Symbol	Parameter	Test Conditions		Min.	Max.	Units
I _{RRM} /I _{DRM}	Peak reverse and off-state current	At V _{RRM} /V _{DRM} , T _{case} = 125°C		-	600	mA
dV/dt	Max. linear rate of rise of off-state voltage	To 67% V _{DRM} , T _j = 125°C, ga	ate open	-	2000	V/µs
dl/dt	Rate of rise of on-state current	From 67% V_{DRM} to 2x $I_{T(AV)}$	Repetitive 50Hz	-	200	A/µs
		Gate source 30V, 10Ω ,	Non-repetitive	-	500	A/µs
		t _r < 0.5µs, T _j = 125°C				
V _{T(TO)}	Threshold voltage – Low level	500 to 4000A at $T_{case} = 125^{\circ}$	С	-	1.03	V
	Threshold voltage – High level	4000 to 8000A at $T_{case} = 125$	5°C	-	1.08	V
r _T	On-state slope resistance – Low level	500A to 4000A at $T_{case} = 125$	5°C	-	0.18	mΩ
	On-state slope resistance – High level	4000A to 8000A at T _{case} = 125°C		-	0.1675	mΩ
t _{gd}	Delay time	$V_D = 67\% V_{DRM}$, gate source	30V, 10Ω	-	3	μs
		$t_r = 0.5 \mu s, T_j = 25^{\circ}C$				
tq	Turn-off time	$I_T = 3000A, T_j = 125^{\circ}C,$ $V_R = 200V, dI/dt = 1A/\mu s,$			700	μs
		$dV_{DR}/dt = 20V/\mu s$ linear				
Qs	Stored charge	I _T = 3000A, Τ _i = 125°C, dI/dt – 1A/μs,		3700	9000	μC
I _{RR}	Reverse recovery current	$V_{\text{Rpeak}} \sim 3900 \text{V}, \text{V}_{\text{R}} \sim 2600 \text{V}$		45	79	A
IL	Latching current	$T_j = 25^{\circ}C, V_D = 5V$		-	3	A
Iн	Holding current	$T_j = 25^{\circ}C, R_{G-K} = \infty, I_{TM} = 500A, I_T = 5A$		-	300	mA

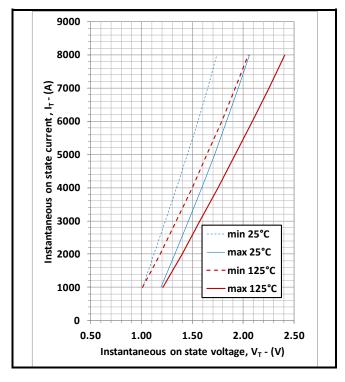


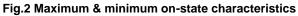


GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
V _{GT}	Gate trigger voltage	$V_{DRM} = 5V, T_{case} = 25^{\circ}C$	1.5	V
V _{GD}	Gate non-trigger voltage	At 50% V _{DRM} , T _{case} = 125°C	0.4	V
I _{GT}	Gate trigger current	$V_{DRM} = 5V, T_{case} = 25^{\circ}C$	350	mA
I _{GD}	Gate non-trigger current	At 50% V _{DRM,} T _{case} = 125°C	10	mA

CURVES





V_{TM} EQUATION

 $V_{TM} = A + Bln (I_T) + C.I_T + D.\sqrt{I_T}$

Where
$$A = 0.751026$$

 $B = 0.043281$
 $C = 0.000160$
 $D = 0$
these values are valid for T_i = 125°C for I_T 500A to 8000A



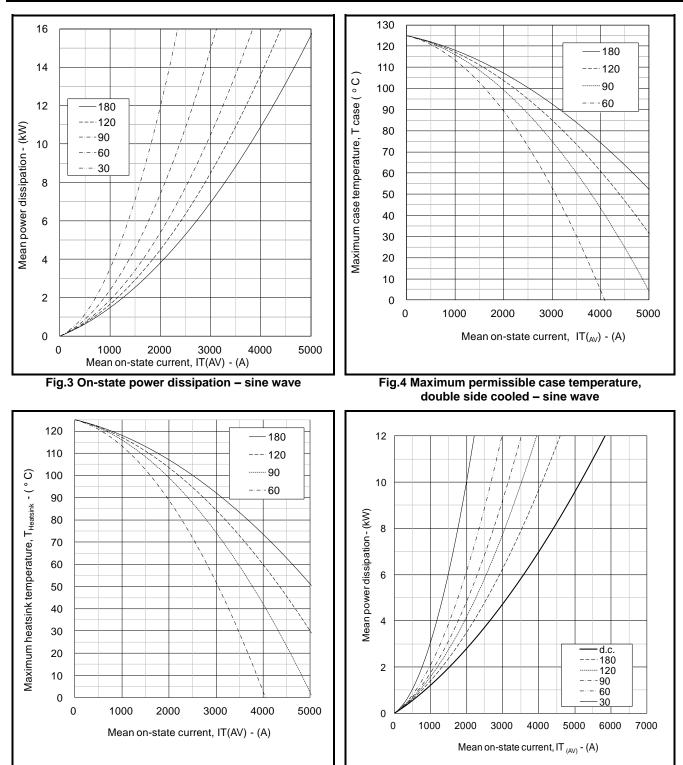
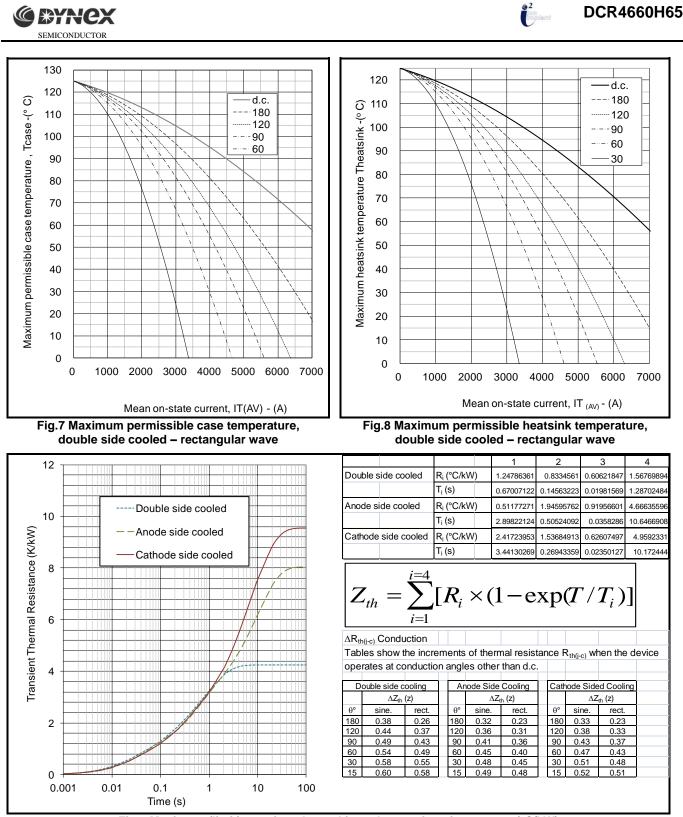
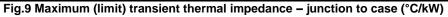


Fig.5 Maximum permissible heatsink temperature, double side cooled – sine wave



DCR4660H65





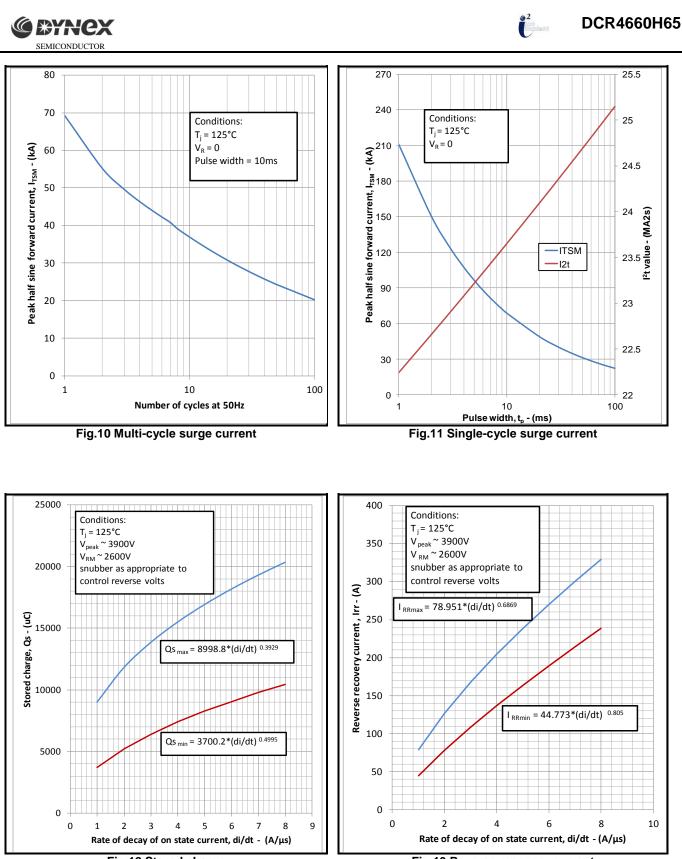
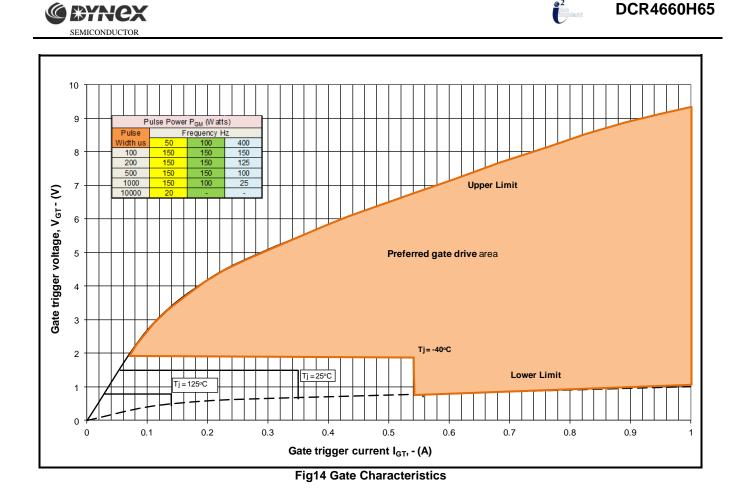


Fig.12 Stored charge

Fig.13 Reverse recovery current



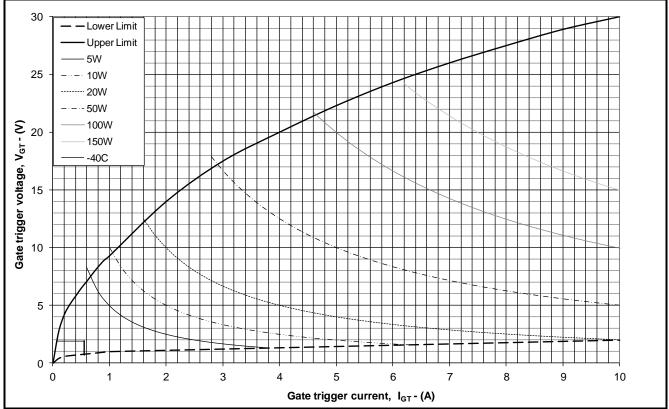


Fig. 15 Gate characteristics



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PACKAGE DETAILS

For further package information, please contact Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.

Device	(mm)	Thickness (mm)	3rd ANGLE PROJECTION · · · DO NOT SCALE IF IN DOUBT ASK
DCRxxxxH42	35.15	34.28	HOLE Ø3.60 X 4.00 DEEP (IN BOTH ELECTRODES)
DCRxxxxH52	35.27	34.4	
DCR4420H65 DCR4660H65	35.3 35.3	34.7 34.7	20° OFFSET (NOMINAL) TO GATE TUBE
DCRxxxxH85	35.65	35.05	
			Ø170±0.3 Ø115 NOM. CATHODE GATE Ø115 NOM. Ø161 MAX.
			Lead length: 420mm Lead terminal connector: M4 ring Package outline type code:H

Fig.16 Package outline





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Extended exposure to conditions outside the product ratings may affect reliability leading to premature product failure. Use outside the product ratings is likely to cause permanent damage to the product. In extreme conditions, as with all semiconductors, this may include potentially hazardous rupture, a large current to flow or high voltage arcing, resulting in fire or explosion. Appropriate application design and safety precautions should always be followed to protect persons and property.

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